

P-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- Advanced trench cell design
- Low Thermal Resistance

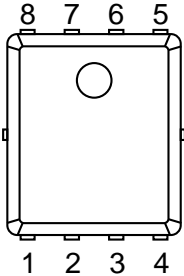
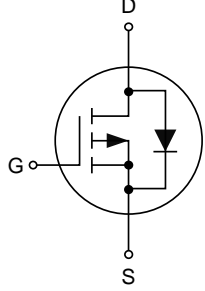
1.2 Applications

- Motor driver
- DC/DC Converter

1.3 Quick reference

- $BV \geq -100V$
- $R_{DS(ON)} \leq 200m\Omega @ V_{GS} = -10V$
- $P_{tot} \leq 35W$
- $R_{DS(ON)} \leq 230m\Omega @ V_{GS} = -4.5V$
- $I_D \leq -20A$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1,2,3	Source	 <p style="text-align: center;">Top View PDFN5x6-8L</p>	
4	Gate		
5,6,7,8	Drain		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C=25^{\circ}C$	-	-100	V
V_{GS}	Gate-Source Voltage	$T_C=25^{\circ}C$	-	± 20	V
I_D^*	Drain Current	$T_C=25^{\circ}C, V_{GS}=10V$	-	-20	A
$I_{DM}^{*,**,***}$	Pulsed Drain Current	$T_C=25^{\circ}C, V_{GS}=10V$	-	-43	A
P_{tot}^*	Total Power Dissipation	$T_C=25^{\circ}C$	-	35	W
T_{stg}	Storage Temperature		-55	150	$^{\circ}C$
T_J	Junction Temperature		-	150	$^{\circ}C$
I_S	Diode Forward Current	$T_C=25^{\circ}C$	-	-43	A
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient		-	62.5	$^{\circ}C/W$
$R_{\theta JC}^*$	Thermal Resistance-Junction to Case		-	3.5	$^{\circ}C/W$

Notes:

* Surface Mounted on 1 in² pad area, $t \leq 10$ sec

** Pulse width $\leq 10\mu s$, duty cycle $\leq 1\%$

*** Limited by bonding wire

4. Marking Information

Product Name	Marking
KJ20P10G	<div style="display: inline-block; background-color: black; color: white; padding: 2px;">20P10 YWWXXX</div> YWW: Date Code

5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ20P10G	PDFN5x6-8L			5000	

Note: KUAJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C)

6. Electrical Characteristics (T_C = 25°C Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
B _{VDS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-100	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.0	-	-2.0	V
I _{DSS}	Drain Leakage Current	V _{DS} =-80V, V _{GS} =0V	-	-	-1	μA
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^a	Channel On-State Resistance	V _{GS} =-10V, I _{DS} =-3A	-	170	200	mΩ
		V _{GS} =-4.5V, I _{DS} =-2A	-	180	230	
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =-3A, V _{GS} =0V	-	-	-1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =-3A, dI _{SD} /dt=100A/μs	-	24.7	-	ns
Q _{rr}	Reverse Recovery Charge		-	28.4	-	nC
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-50V Frequency=1MHz	-	1503	-	pF
C _{oss}	Output Capacitance		-	38	-	
C _{rss}	Reverse Transfer Capacitance		-	34	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} =-50V, V _{GEN} =-10V, R _G =4.5Ω, R _L =16.6Ω, I _{DS} =-3A	-	9.9	-	ns
t _r	Turn-on Rise Time		-	29.2	-	
t _{d(off)}	Turn-off Delay Time		-	276	-	
t _f	Turn-off Fall Time		-	84.5	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-50V, I _{DS} =-3A	-	23	-	nC
Q _{gs}	Gate-Source Charge		-	6.5	-	
Q _{gd}	Gate-Drain Charge		-	3	-	

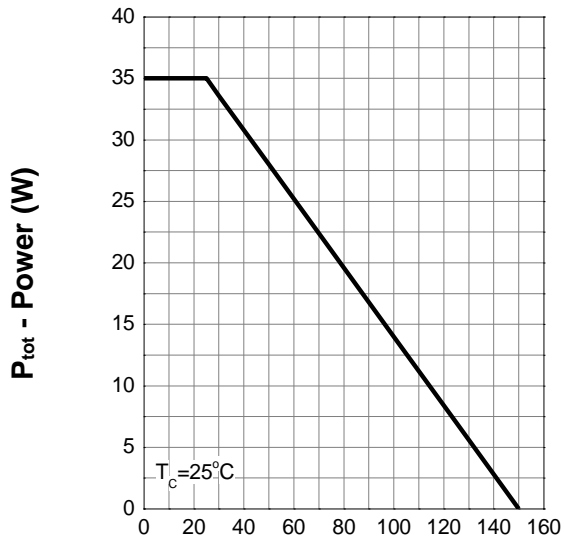
Notes:

a: Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %

b: Guaranteed by design, not subject to production testing

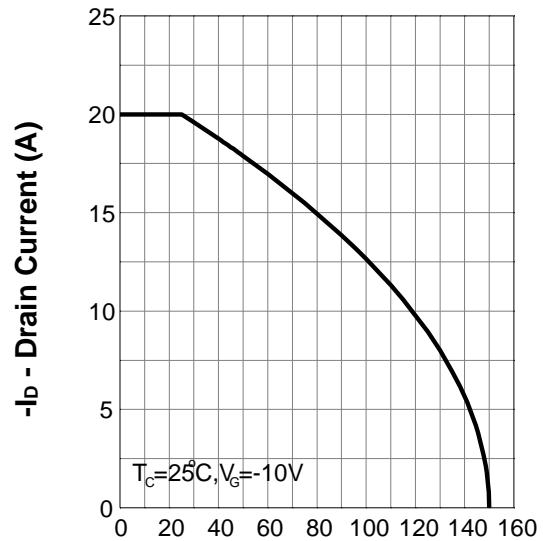
7. Typical Characteristics

Power Dissipation



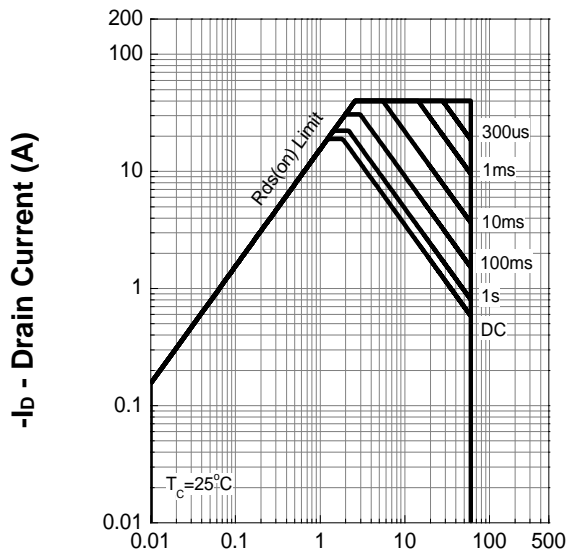
T_j - Junction Temperature ($^\circ\text{C}$)

Drain Current



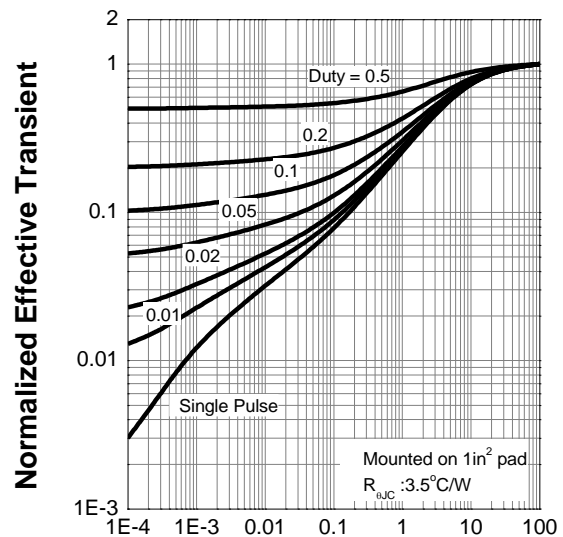
T_j - Junction Temperature ($^\circ\text{C}$)

Safe Operation Area



$-V_{DS}$ - Drain-Source Voltage (V)

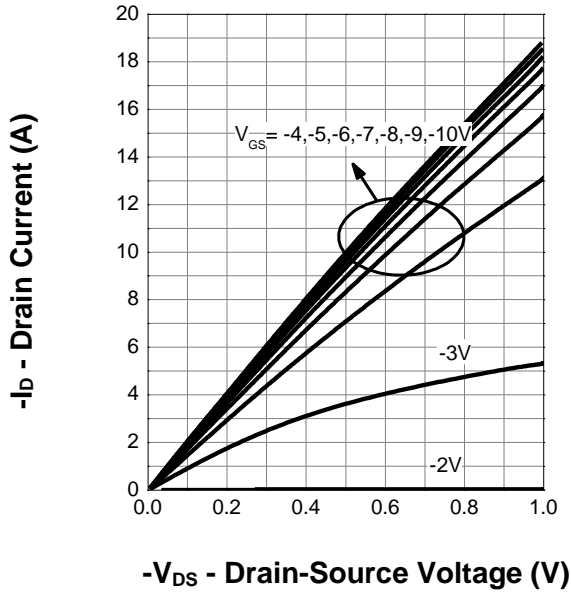
Thermal Transient Impedance



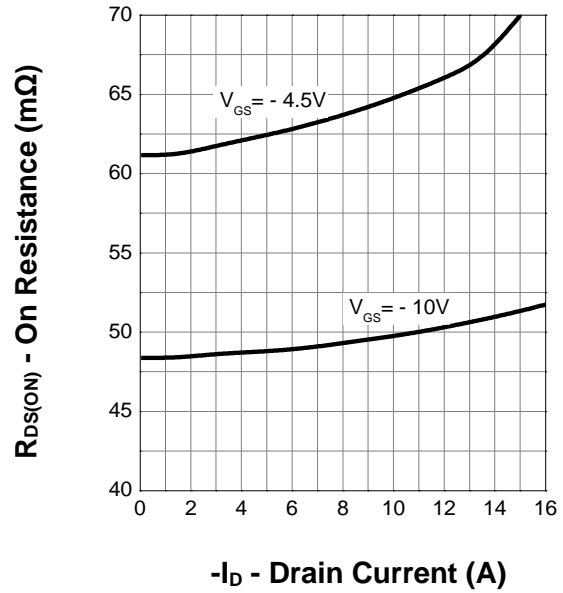
Square Wave Pulse Duration (sec)

7. Typical Characteristics (cont.)

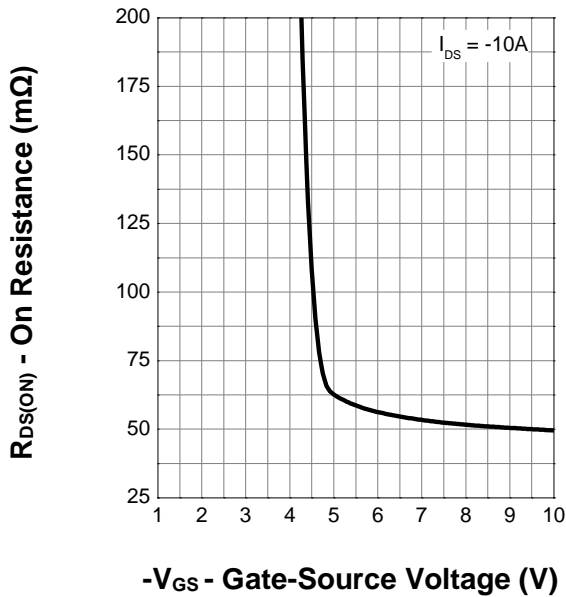
Output Characteristics



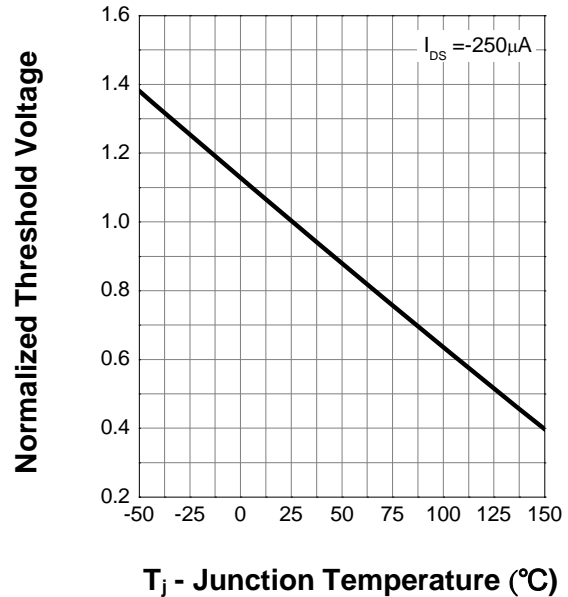
Drain-Source On Resistance



Transfer Characteristics

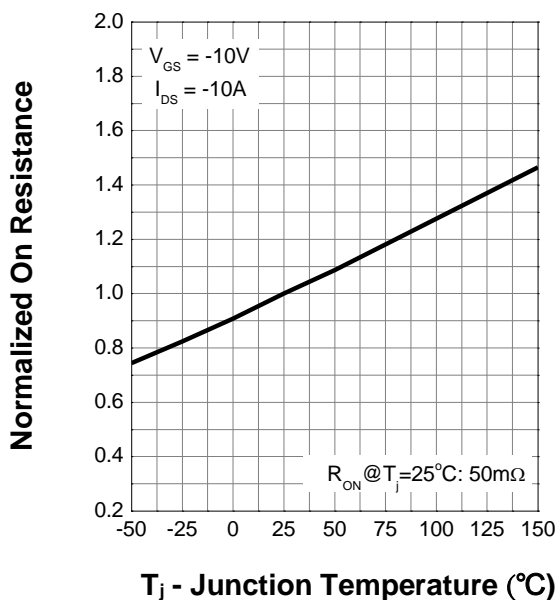


Gate Threshold Voltage

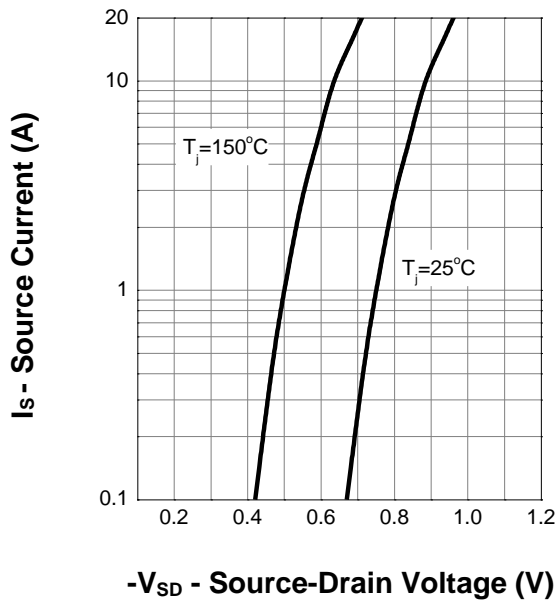


7. Typical Characteristics (cont.)

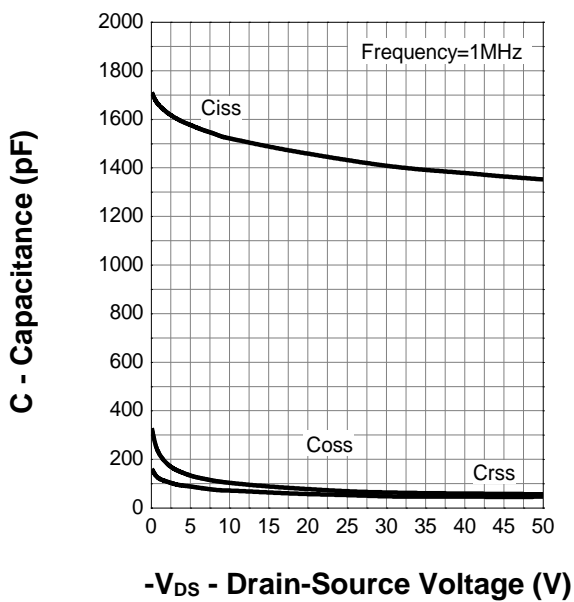
Drain-Source On Resistance



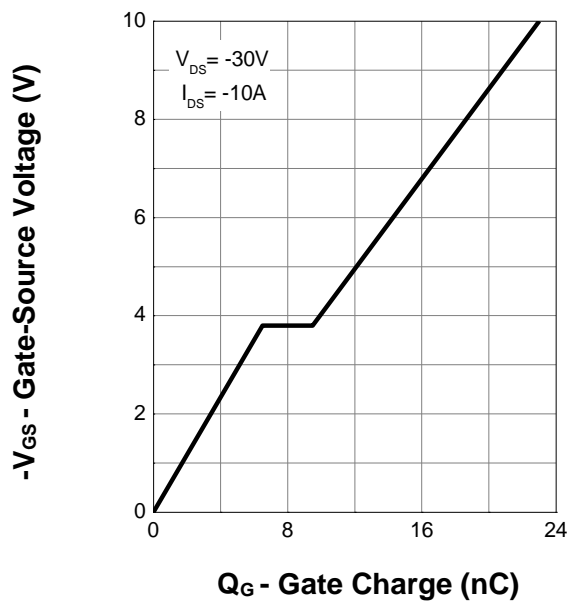
Source-Drain Diode Forward



Capacitance

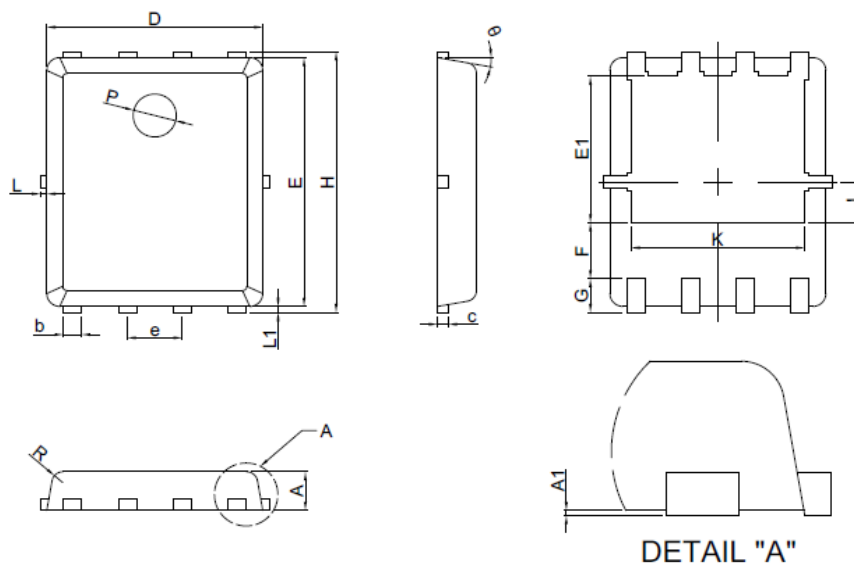


Gate Charge



8.Package Dimensions

PDFN5x6-8L Package



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	0.80	1.00
A1	0.00	0.05
b	0.35	0.49
c	0.254REF	
D	4.90	5.10
F	1.40REF	
E	5.70	5.90
e	1.27BSC	
H	5.95	6.20
L1	0.10	0.18
G	0.60REF	
K	4.00REF	
L	-	0.15
J	0.95BSC	
P	1.00REF	
E1	3.40REF	
θ	6°	14°
R	0.25REF	